

Figure 1: Vertically matched Thermal N-port generated directly from analytical solution of the heat diffusion equation, and represented by thermal impedance matrix, $R_{TH_{ij}}(s)$ with varying temperatures at the top and bottom surface.

REEDATM Form: thermalblock:(instance name) < power generating device terminals, top surface discretization terminals, top terminals for patch1, top terminals for patch2, bottom surface discretization terminals, bottom terminals for patch1, bottom terminals for patch2, thermal ground> <parameter list>

Example:

```
thermalblock:test1 1 2 3 4 5 101 102 103 104 105 106 107 108 109 110 111 112 113 114 +115 116
117 201 202 203 204 205 206 207 +208 209 210 211 212 213 214 215 216 217 1002
+Ntimesteps=nsteps dt=deltat Tambient=temp time_d=1 msubstrate=3 read_input=0
+filename="Die_Rth.dat" l=1624e-6 w=1470e-6 d=100e-6 rho=5320 c=350 ks=46 xi=0 ndevices=5
+mmax=50 nmax=50 ppatch=2
```

Model Parameters:

Name	Description	Units	Default
nimesteps	Number of time steps in transient simulation		0
dt	Length of timestep	s	0.0
tambient	Ambient Temperature	K	300.0
time_d	Flag if true calculate in the time domain.		False
read_input	Flag read_input thermal resistance matrices from file.		False
l	Substrate x-dimension.	m	0.05
w	Substrate y-dimension.	m	0.05
d	Substrate z-dimension.	m	0.0016
Ks	Thermal conductivity	W/m.K	0.294
rho	Density	(kg.m-3)	1900
C	Specific heat	J/kg.K	1150
xi	Adjustment for T**4 non linearity		1.3
eta	Adjustment for natural convection		3.0
epsilon	Emissivity		0.7
narray	Order of NxN grid array		4
ndevices	Number of heat dissipating devices		16
msubstrate	Order of MxM substrate surface discretisation		3
b	Exponent of temperature dependence of thermal conductivity		0.0
nmax	Maximum number of basis states in X direction		100
mmax	Maximum number of basis states in Y direction		100
filename	Filename to read the Rth from		
ppatch	Order of MxM patch surface discretisation		0
ofilename	Filename to write the temperature to		

Multiple Models

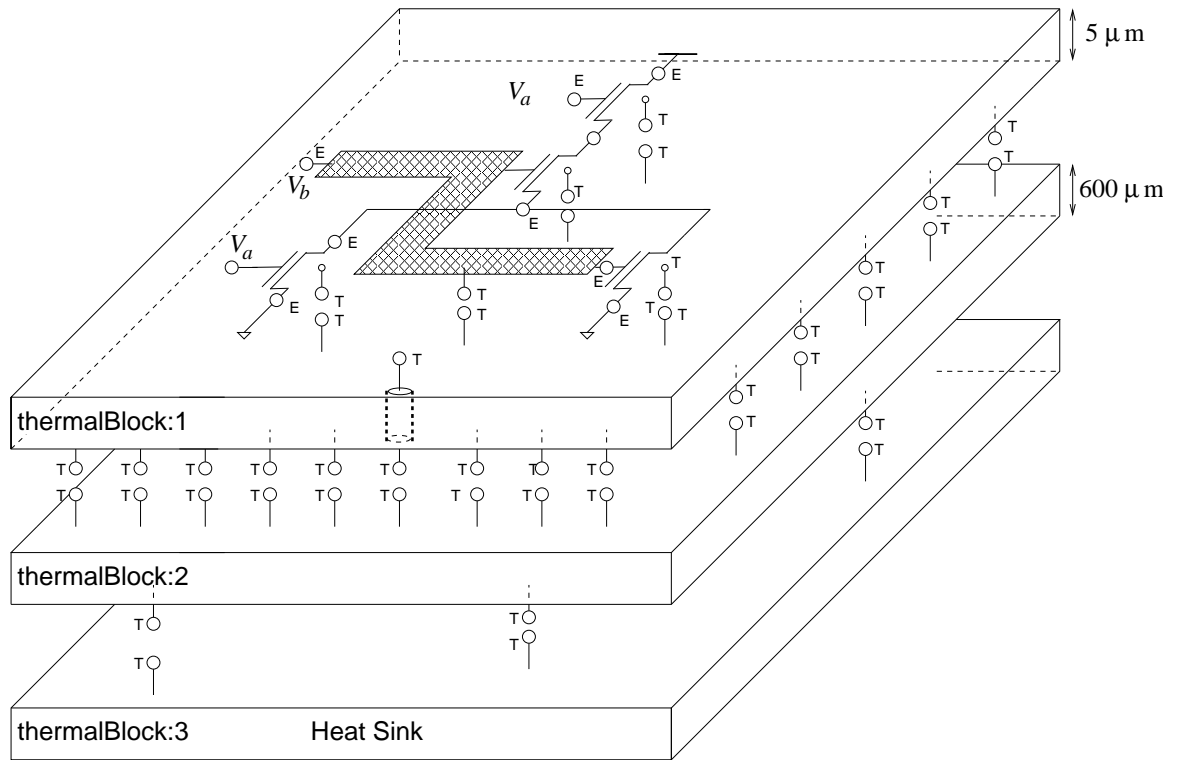


Figure 2: Connecting multiple thermal Nport elements.

Standard Calculations

$$R_{TH_{ii'}}^{00} = \frac{1}{\kappa_s LW} \sum_{mn} \frac{4 \coth \gamma_{mn} D}{(1 + \delta_{m0})(1 + \delta_{n0}) \gamma_{mn}} \frac{I_{mn}^{0i}}{I_{00}^{0i}} \frac{I_{mn}^{0i'}}{I_{00}^{0j}} \quad (1)$$

$$R_{TH_{ij}}^{0D} = \frac{1}{\kappa_s LW} \sum_{mn} \frac{-4 \operatorname{cosech} \gamma_{mn} D}{(1 + \delta_{m0})(1 + \delta_{n0}) \gamma_{mn}} \frac{I_{mn}^{0i}}{I_{00}^{0i}} \frac{I_{mn}^{Dj}}{I_{00}^{Dj}} \quad (2)$$

$$R_{TH_{ji}}^{D0} = \frac{1}{\kappa_s LW} \sum_{mn} \frac{4 \operatorname{cosech} \gamma_{mn} D}{(1 + \delta_{m0})(1 + \delta_{n0}) \gamma_{mn}} \frac{I_{mn}^{Dj}}{I_{00}^{Dj}} \frac{I_{mn}^{0i}}{I_{00}^{0i}} \quad (3)$$

$$R_{TH_{jj'}}^{DD} = \frac{1}{\kappa_s LW} \sum_{mn} \frac{-4 \coth \gamma_{mn} D}{(1 + \delta_{m0})(1 + \delta_{n0}) \gamma_{mn}} \frac{I_{mn}^{Dj}}{I_{00}^{Dj}} \frac{I_{mn}^{Dj'}}{I_{00}^{Dj'}} \quad (4)$$

Bugs:

Frequency domain model not implemented.


Number of patches hardwired as 2.

Position of the power generating devices fixed.

Version:

2006.05.01

Credits:

Name	Affiliation	Date	
Sonali Luniya	North Carolina State University	May 2006	
William Batty	Filtronic Compound Semiconductors, UK	May 2006	
Carlos Christoffersen	Lakehead University, Canada	May 2006	

Publications:

1. Sonali Luniya, William Batty, Vincent Caccamesi, Mikael Garcia, Carlos Christoffersen, Samson Melamed, W. Rhett Davis, and Michael Steer, ‘‘Compact Electrothermal Modeling of an X-band MMIC,’’ *2006 IEEE International Microwave Symposium*, June 11 2006.